Analog Multiplexer / **Demultiplexer**

High-Performance Silicon-Gate CMOS

The MC74LVX8051 utilizes silicon-gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. This analog multiplexer/demultiplexer controls analog voltages that may vary across the complete power supply range (from VCC to GND).

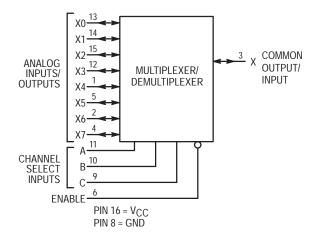
The LVX8051 is similar in pinout to the high-speed HC4051A and the metal-gate MC14051B. The Channel-Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel–Select and Enable inputs are compatible with standard CMOS outputs; with pull-up resistors they are compatible with LSTTL outputs.

This device has been designed so that the ON resistance (R_{on}) is more linear over input voltage than Ron of metal-gate CMOS analog switches.

- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Analog Power Supply Range $(V_{CC} GND) = 2.0 \text{ to } 6.0 \text{ V}$
- Digital (Control) Power Supply Range $(V_{CC} GND) = 2.0$ to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal-Gate Counterparts
- Low Noise
- In Compliance With the Requirements of JEDEC Standard No. 7A
- Chip Complexity: LVX8051 184 FETs or 46 Equivalent Gates

LOGIC DIAGRAM MC74LVX8051 Single-Pole, 8-Position Plus Common Off





ON Semiconductor

Formerly a Division of Motorola

http://onsemi.com

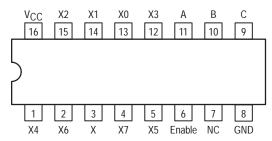




16-LEAD SOIC **D SUFFIX** CASE 751B

16-LEAD TSSOP **DT SUFFIX** CASE 948F

PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 11 of this data sheet.

ORDERING INFORMATION

Device	Device Package	
MC74LVX8051D	SOIC	48 Units/Rail
MC74LVX8051DT	TSSOP	96 Units/Rail

FUNCTION TABLE - MC74LVX8051

Control Inputs				
Enable	С	Select		ON Channels
Enable	C	В	Α	ON Channels
L	L	L	L	X0
L	L	L	Н	X1
L	L	Н	L	X2
L	L	Н	Н	X3
L	Н	L	L	X4
L	Н	L	Н	X5
L	Н	Н	L	X6
L	Н	Н	Н	X7
Н	Х	Х	Х	NONE

X = Don't Care

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	Positive DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
VIS	Analog Input Voltage	-0.5 to V _{CC} + 0.5	V
V _{in}	Digital Input Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
I	DC Current, Into or Out of Any Pin	± 20	mA
PD	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	∘C

^{*}Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
VCC	Positive DC Supply Voltage (Referenced to GND)	2.0	6.0	V
VIS	Analog Input Voltage	0.0	Vcc	V
V _{in}	Digital Input Voltage (Referenced to GND)	GND	Vcc	V
V _{IO} *	Static or Dynamic Voltage Across Switch		1.2	V
TA	Operating Temperature Range, All Package Types	- 55	+ 85	∘C
t _r , t _f	Input Rise/Fall Time (Channel Select or Enable Inputs)			ns/V
	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	

^{*}For voltage drops across switch greater than 1.2 V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

[†]Derating — SOIC Package: – 7 mW/° C from 65° to 125° C TSSOP Package: – 6.1 mW/° C from 65° to 125° C

DC CHARACTERISTICS — Digital Section (Voltages Referenced to GND)

			vcc	Guara	nteed Lin	nit	
Symbol	Parameter	Condition	V	–55 to 25°C	≤85°C	≤125°C	Unit
VIH	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs	R _{on} = Per Spec	2.0 3.0 4.5 5.5	1.50 2.10 3.15 3.85	1.50 2.10 3.15 3.85	1.50 2.10 3.15 3.85	V
VIL	Maximum Low-Level Input Voltage, Channel-Select or Enable Inputs	R _{on} = Per Spec	2.0 3.0 4.5 5.5	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	V
l _{in}	Maximum Input Leakage Current, Channel–Select or Enable Inputs	V _{in} = V _{CC} or GND	5.5	± 0.1	± 1.0	± 1.0	μА
Icc	Maximum Quiescent Supply Current (per Package)	Channel Select, Enable and V _{IS} = V _{CC} or GND; V _{IO} = 0 V	5.5	4.0	40	160	μА

DC ELECTRICAL CHARACTERISTICS Analog Section

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25° C	≤ 85°C	≤ 125°C	Unit
R _{on}	Maximum "ON" Resistance	$V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}}$ $V_{\text{IS}} = V_{\text{CC}} \text{ to GND}$ $ I_{\text{S}} \le 10.0 \text{ mA (Figures 1, 2)}$	3.0 4.5 5.5	30 25 20	35 28 25	40 35 30	Ω
		$V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}}$ $V_{\text{IS}} = V_{\text{CC}} \text{ or GND (Endpoints)}$ $ I_{\text{S}} \le 10.0 \text{ mA (Figures 1, 2)}$	3.0 4.5 5.5	30 25 20	35 28 25	40 35 30	
ΔR _{on}	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$V_{\text{IN}} = V_{\text{IL}} \text{ or } V_{\text{IH}}$ $V_{\text{IS}} = 1/2 (V_{\text{CC}} - \text{GND})$ $ I_{\text{S}} \le 10.0 \text{ mA}$	3.0 4.5 5.5	15 8.0 8.0	20 12 12	25 15 15	Ω
l _{off}	Maximum Off–Channel Leakage Current, Any One Channel	V _{in} = V _{IL} or V _{IH} ; V _{IO} = V _{CC} or GND; Switch Off (Figure 3)	5.5	0.1	0.5	1.0	μА
	Maximum Off–Channel Leakage Current, Common Channel	V _{in} = V _{IL} or V _{IH} ; V _{IO} = V _{CC} or GND; Switch Off (Figure 4)	5.5	0.2	2.0	4.0	
l _{on}	Maximum On–Channel Leakage Current, Channel–to–Channel	V _{in} = V _{IL} or V _{IH} ; Switch–to–Switch = V _{CC} or GND; (Figure 5)	5.5	0.2	2.0	4.0	μА

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 3 \text{ ns}$)

		VCC	Gu	aranteed Lim	nit	
Symbol	Parameter	V	–55 to 25°C	≤85°C	≤125°C	Unit
tPLH, tPHL	Maximum Propagation Delay, Channel–Select to Analog Output (Figure 9)	2.0 3.0 4.5 5.5	30 20 15 15	35 25 18 18	40 30 22 20	ns
^t PLH [,] ^t PHL	Maximum Propagation Delay, Analog Input to Analog Output (Figure 10)	2.0 3.0 4.5 5.5	4.0 3.0 1.0 1.0	6.0 5.0 2.0 2.0	8.0 6.0 2.0 2.0	ns
^t PLZ [,] ^t PHZ	Maximum Propagation Delay, Enable to Analog Output (Figure 11)	2.0 3.0 4.5 5.5	30 20 15 15	35 25 18 18	40 30 22 20	ns
tPZL, tPZH	Maximum Propagation Delay, Enable to Analog Output (Figure 11)	2.0 3.0 4.5 5.5	20 12 8.0 8.0	25 14 10 10	30 15 12 12	ns
C _{in}	Maximum Input Capacitance, Channel–Select or Enable Inputs		10	10	10	pF
C _{I/O}	Maximum Capacitance Analog I/O		35	35	35	pF
	(All Switches Off) Common O/I		130	130	130	1
	Feedthrough		1.0	1.0	1.0	1

C _{PD}		Typical @ 25°C, V _{CC} = 5.0 V	pF
	Power Dissipation Capacitance (Figure 13)*	45	

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$.

ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

			vcc	Limit*	
Symbol	Parameter	Condition	V	25°C	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 6)	f_{in} = 1MHz Sine Wave; Adjust f_{in} Voltage to Obtain 0dBm at V _{OS} ; Increase f_{in} Frequency Until dB Meter Reads –3dB; R_L = 50 Ω , C_L = 10pF	3.0 4.5 5.5	80 80 80	MHz
_	Off–Channel Feedthrough Isolation (Figure 7)	f_{in} = Sine Wave; Adjust f_{in} Voltage to Obtain 0dBm at V _{IS} f_{in} = 10kHz, R _L = 600 Ω , C _L = 50pF	3.0 4.5 5.5	-50 -50 -50	dB
		f _{in} = 1.0MHz, R _L = 50Ω, C _L = 10pF	3.0 4.5 5.5	−37 −37 −37	
_	Feedthrough Noise. Channel–Select Input to Common I/O (Figure 8)	$V_{in} \le 1 \text{MHz Square Wave } (t_{\Gamma} = t_{\bar{f}} = 6 \text{ns}); \text{ Adjust R}_L $ at Setup so that $I_S = 0 \text{A};$ Enable = GND $R_L = 600 \Omega, C_L = 50 \text{pF}$	3.0 4.5 5.5	25 105 135	mVpp
		R _L = 10kΩ, C _L = 10pF	3.0 4.5 5.5	35 145 190	
THD	Total Harmonic Distortion (Figure 14)	$\begin{aligned} f_{in} &= 1 \text{kHz}, R_L = 10 \text{k}\Omega, C_L = 50 \text{pF} \\ \text{THD} &= \text{THD}_{measured} - \text{THD}_{source} \\ & \text{V}_{IS} = 2.0 \text{Vpp sine wave} \\ & \text{V}_{IS} = 4.0 \text{Vpp sine wave} \\ & \text{V}_{IS} = 5.0 \text{Vpp sine wave} \end{aligned}$	3.0 4.5 5.5	0.10 0.08 0.05	%

^{*}Limits not tested. Determined by design and verified by qualification.

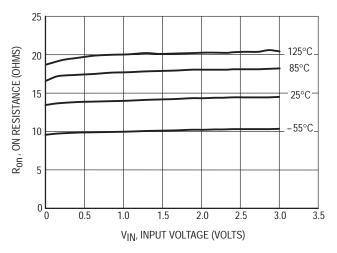


Figure 1a. Typical On Resistance, V_{CC} = 3.0 V

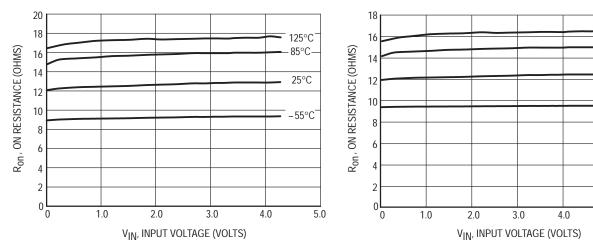


Figure 1b. Typical On Resistance, $V_{CC} = 4.5 \text{ V}$

Figure 1c. Typical On Resistance, $V_{CC} = 5.5 \text{ V}$

125°C

85°C

25°C

- 55°C

6.0

5.0

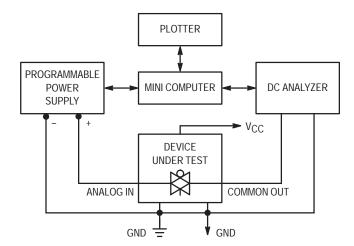


Figure 2. On Resistance Test Set-Up

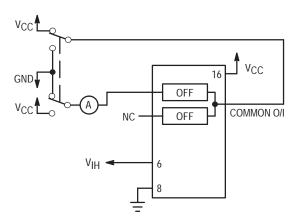


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

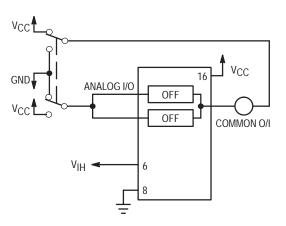


Figure 4. Maximum Off Channel Leakage Current, Common Channel, Test Set-Up

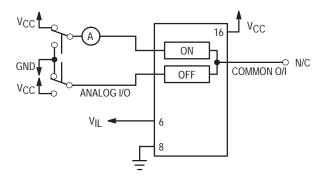


Figure 5. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

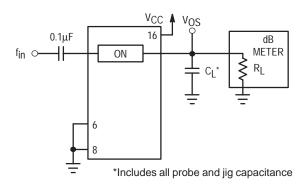


Figure 6. Maximum On Channel Bandwidth, Test Set-Up

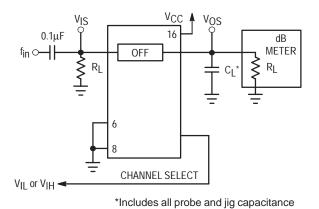
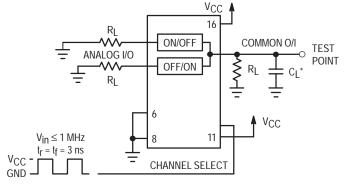


Figure 7. Off Channel Feedthrough Isolation,
Test Set-Up



*Includes all probe and jig capacitance

Figure 8. Feedthrough Noise, Channel Select to Common Out, Test Set-Up

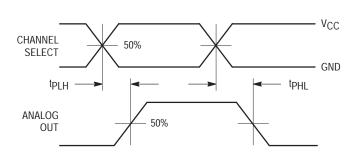
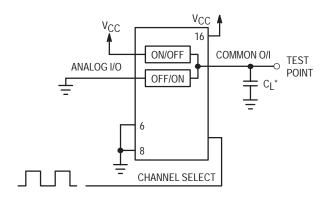


Figure 9a. Propagation Delays, Channel Select to Analog Out



*Includes all probe and jig capacitance

Figure 9b. Propagation Delay, Test Set-Up Channel Select to Analog Out

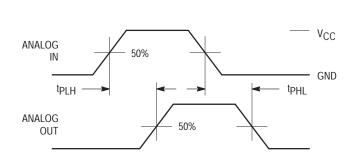
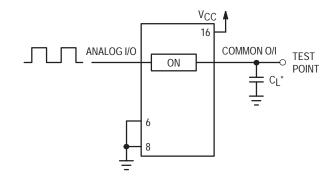


Figure 10a. Propagation Delays, Analog In to Analog Out



*Includes all probe and jig capacitance

Figure 10b. Propagation Delay, Test Set-Up
Analog In to Analog Out

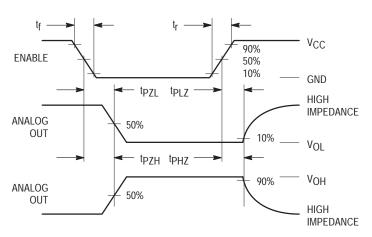


Figure 11a. Propagation Delays, Enable to Analog Out

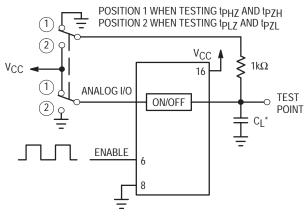
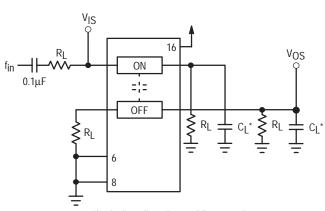


Figure 11b. Propagation Delay, Test Set-Up Enable to Analog Out



*Includes all probe and jig capacitance

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up

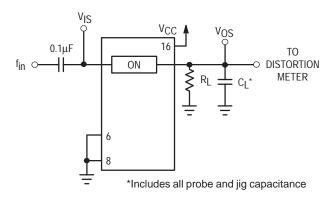


Figure 14a. Total Harmonic Distortion, Test Set-Up

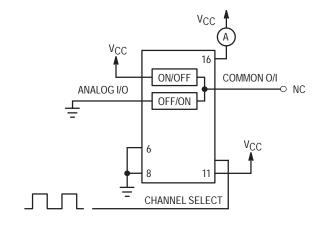


Figure 13. Power Dissipation Capacitance,
Test Set-Up

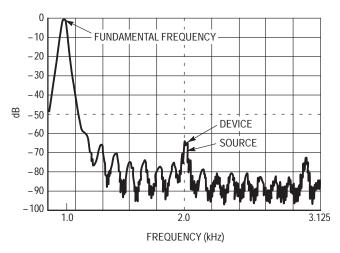


Figure 14b. Plot, Harmonic Distortion

APPLICATIONS INFORMATION

The Channel Select and Enable control pins should be at V_{CC} or GND logic levels. V_{CC} being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC} = +5V = logic high$$

 $GND = 0V = logic low$

The maximum analog voltage swing is determined by the supply voltage V_{CC}. The positive peak analog voltage should not exceed V_{CC}. Similarly, the negative peak analog voltage should not go below GND. In this example, the difference between V_{CC} and GND is five volts. Therefore, using the configuration of Figure 15, a maximum analog signal of five volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not

connected). However, tying unused analog inputs and outputs to V_{CC} or GND through a low value resistor helps minimize crosstalk and feedthrough noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$V_{CC}$$
 – GND = 2 to 6 volts

When voltage transients above V_{CC} and/or below GND are anticipated on the analog channels, external Germanium or Schottky diodes (D_x) are recommended as shown in Figure 16. These diodes should be able to absorb the maximum anticipated current surges during clipping.

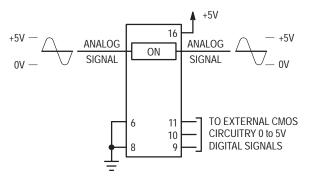


Figure 15. Application Example

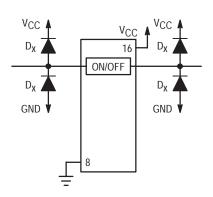
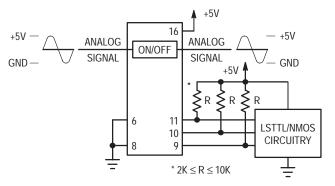
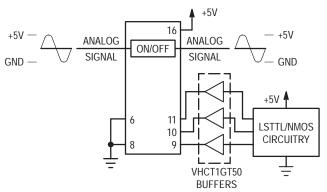


Figure 16. External Germanium or **Schottky Clipping Diodes**



a. Using Pull-Up Resistors



b. Using HCT Interface

Figure 17. Interfacing LSTTL/NMOS to CMOS Inputs

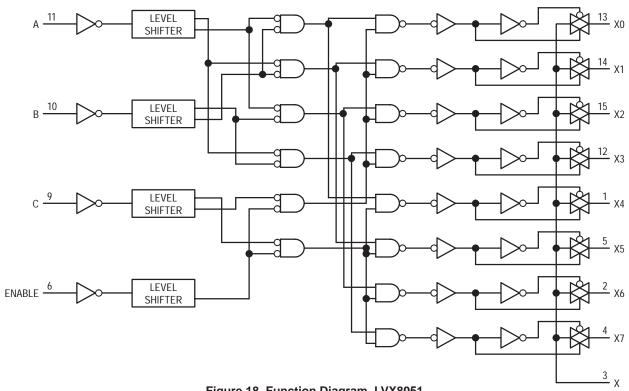
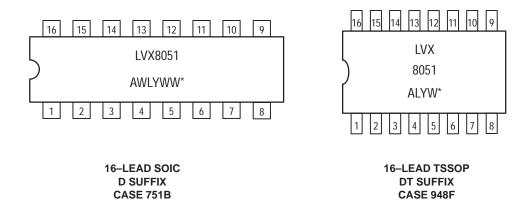


Figure 18. Function Diagram, LVX8051

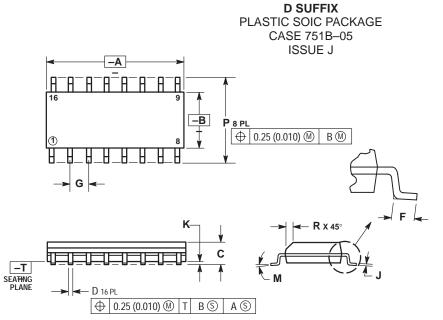
MARKING DIAGRAMS

(Top View)



*See Applications Note #AND8004/D for date code and traceability information.

PACKAGE DIMENSIONS



- NOTES:

 1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2 CONTROLLING DIMENSION: MILLIMETER.

 3 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

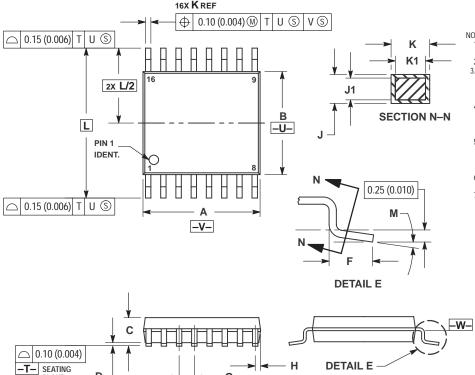
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.2	7 BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

DT SUFFIX

PLASTIC TSSOP PACKAGE CASE 948F-01 **ISSUE O**



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
- Y 14.3M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH.
 PROTRUSIONS OR GATE BURRS. MOLD FLASH OR
 GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER
- SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED
- 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION
 SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR
 DEETEDBLICE ONLY.
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	0.65 BSC		BSC	
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0°	8°	0°	80	

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular without duties to any products refer in Science in warranty, representation or guarantee regarding the statistically disclaims any and all liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

USA/EUROPE Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line*: 303-675-2167

800-344-3810 Toll Free USA/Canada *To receive a Fax of our publications

N. America Technical Support: 800-282-9855 Toll Free USA/Canada

ASIA/PACIFIC: LDC for ON Semiconductor - Asia Support

Phone: 303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time)

Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-8549

Phone: 81-3-5487-8345 Email: r14153@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative a Sheet 4U.com